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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I²S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 14x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151cct7tr

1 Introduction

This datasheet provides the ordering information and mechanical device characteristics of the STM32L151xC and STM32L152xC ultra-low-power ARM® Cortex®-M3 based microcontroller product line with a Flash memory of 256 Kbytes.

The ultra-low-power STM32L151xC and STM32L152xC family includes devices in 6 different package types: from 48 pins to 100 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the ultra-low-power STM32L151xC and STM32L152xC microcontroller family suitable for a wide range of applications:

- Medical and handheld equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, wired and wireless sensors, video intercom
- Utility metering

This STM32L151xC and STM32L152xC datasheet should be read in conjunction with the STM32L1xxxx reference manual (RM0038). The application note “Getting started with STM32L1xxxx hardware development” (AN3216) gives a hardware implementation overview. Both documents are available from the STMicroelectronics website *www.st.com*.

For information on the ARM® Cortex®-M3 core please refer to the ARM® Cortex®-M3 technical reference manual, available from the www.arm.com website. *Figure 1* shows the general block diagram of the device family.

- **Stop** mode without RTC

  Stop mode achieves the lowest power consumption while retaining the RAM and register contents. All clocks are stopped, the PLL, MSI RC, HSI and LSI RC, LSE and HSE crystal oscillators are disabled. The voltage regulator is in the low-power mode. The device can be woken up from Stop mode by any of the EXTI line, in 8 µs. The EXTI line source can be one of the 16 external lines. It can be the PVD output, the Comparator 1 event or Comparator 2 event (if internal reference voltage is on). It can also be wakened by the USB wakeup.

- **Standby** mode with RTC

  Standby mode is used to achieve the lowest power consumption and real time clock. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI RC and HSE crystal oscillators are also switched off. The LSE or LSI is still running. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

  The device exits Standby mode in 60 µs when an external reset (NRST pin), an IWDG reset, a rising edge on one of the three WKUP pins, RTC alarm (Alarm A or Alarm B), RTC tamper event, RTC timestamp event or RTC Wakeup event occurs.

- **Standby** mode without RTC

  Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire V_{CORE} domain is powered off. The PLL, MSI RC, HSI and LSI RC, HSE and LSE crystal oscillators are also switched off. After entering Standby mode, the RAM and register contents are lost except for registers in the Standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE Crystal 32K osc, RCC_CSR).

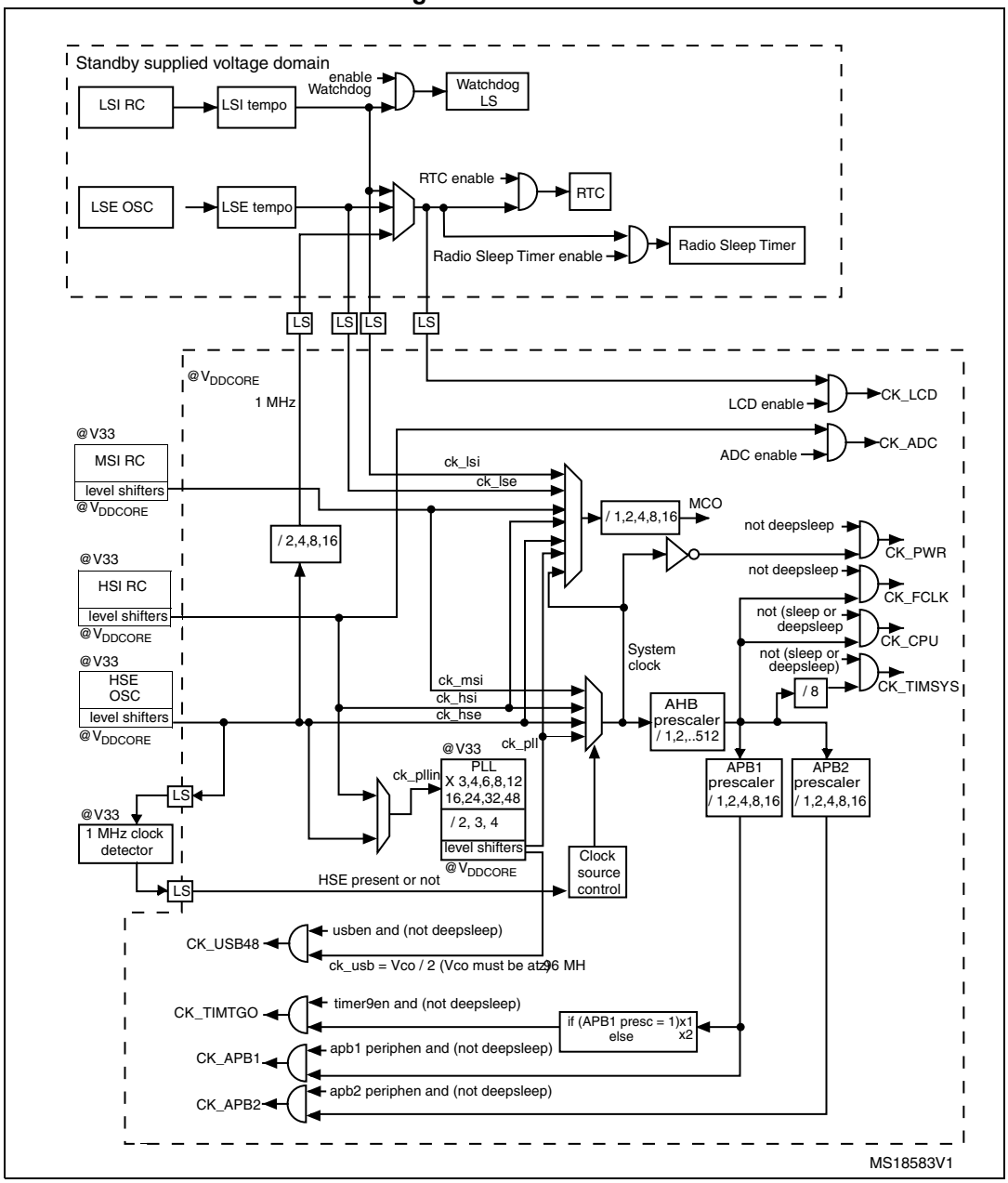
  The device exits Standby mode in 60 µs when an external reset (NRST pin) or a rising edge on one of the three WKUP pin occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped automatically by entering Stop or Standby mode.

Table 3. Functionalities depending on the operating power supply range

	Functionalities depending on the operating power supply range			
Operating power supply range	**DAC and ADC operation**	**USB**	**Dynamic voltage scaling range**	**I/O operation**
V_{DD}= V_{DDA} = 1.65 to 1.71 V	Not functional	Not functional	Range 2 or Range 3	Degraded speed performance
V_{DD}=V_{DDA}= 1.71 to 1.8 V(1)	Not functional	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance
V_{DD}=V_{DDA}= 1.8 to 2.0 V(1)	Conversion time up to 500 Ksps	Not functional	Range 1, Range 2 or Range 3	Degraded speed performance

Figure 2. Clock tree



3.7 Memories

The STM32L151xC and STM32L152xC devices have the following features:

- 32 Kbytes of embedded RAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
  - 256 Kbytes of embedded Flash program memory
  - 8 Kbytes of data EEPROM
  - Options bytes

  The options bytes are used to write-protect or read-out protect the memory (with 4 Kbytes granularity) and/or readout-protect the whole memory with the following options:
  - Level 0: no readout protection
  - Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
  - Level 2: chip readout protection, debug features (ARM Cortex-M3 JTAG and serial wire) and boot in RAM selection disabled (JTAG fuse)

  The whole non-volatile memory embeds the error correction code (ECC) feature.

  The user area of the Flash memory can be protected against Dbus read access by PCROP feature (see RM0038 for details).

3.8 DMA (direct memory access)

The flexible 12-channel, general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each channel is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I^2C, USART, general-purpose timers, DAC and ADC.

Table 9. STM32L151xC and STM32L152xC pin definitions (continued)

Pins					Pin name	Pin type[1]	I / O Structure	Main function[2] (after reset)	Pin functions	
UFBGA100	LQFP100	LQFP64	WLCSP63	LQFP48 or UFQFPN48					Alternate functions	Additional functions
E11	64	38	E1	-	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/ LCD_SEG25	-
E10	65	39	D1	-	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26	-
D12	66	40	E2	-	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27	-
D11	67	41	E3	29	PA8	I/O	FT	PA8	USART1_CK/MCO/ LCD_COM0	-
D10	68	42	C1	30	PA9	I/O	FT	PA9	USART1_TX/ LCD_COM1	-
C12	69	43	D2	31	PA10	I/O	FT	PA10	USART1_RX/ LCD_COM2	-
B12	70	44	B1	32	PA11	I/O	FT	PA11	USART1_CTS/ SPI1_MISO	USB_DM
A12	71	45	D3	33	PA12	I/O	FT	PA12	USART1_RTS/ SPI1_MOSI	USB_DP
A11	72	46	C2	34	PA13	I/O	FT	JTMS-SWDIO	JTMS-SWDIO	-
C11	73	-	-	-	PH2	I/O	FT	PH2	-	-
F11	74	47	A1	35	V_{SS_2}	S	-	V_{SS_2}	-	-
G11	75	48	B2	36	V_{DD_2}	S	-	V_{DD_2}	-	-
A10	76	49	C3	37	PA14	I/O	FT	JTCK-SWCLK	JTCK-SWCLK	-
A9	77	50	A2	38	PA15	I/O	FT	JTDI	TIM2_CH1_ETR/ SPI1_NSS/ SPI3_NSS/I2S3_WS/ LCD_SEG17/JTDI	-
B11	78	51	B3	-	PC10	I/O	FT	PC10	SPI3_SCK/I2S3_CK/ USART3_TX/ LCD_SEG28/ LCD_SEG40/ LCD_COM4	-

Table 10. Alternate function input/output (continued)

Port name	Digital alternate function number												
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	. .	AFIO11	. .	AFIO14	AFIO15
	Alternate function												
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3		LCD		CPRI	SYSTEM
PD3	-	-	-	-	-	SPI2_MISO	-	USART2_CTS		-		TIMx_IC4	EVENT OUT
PD4	-	-	-	-	-	SPI2_MOSI I2S2_SD	-	USART2_RTS		-		TIMx_IC1	EVENT OUT
PD5	-	-	-	-	-		-	USART2_TX		-		TIMx_IC2	EVENT OUT
PD6	-	-	-		-	-	-	USART2_RX		-		TIMx_IC3	EVENT OUT
PD7	-	-	-	TIM9_CH2	-	-	-	USART2_CK		-		TIMx_IC4	EVENT OUT
PD8	-	-	-	-	-	-	-	USART3_TX		SEG28		TIMx_IC1	EVENT OUT
PD9	-	-	-	-	-	-	-	USART3_RX		SEG29		TIMx_IC2	EVENT OUT
PD10	-	-	-	-	-	-	-	USART3_CK		SEG30		TIMx_IC3	EVENT OUT
PD11	-	-	-	-	-	-	-	USART3_CTS		SEG31		TIMx_IC4	EVENT OUT
PD12	-	-	TIM4_CH1	-	-	-	-	USART3_RTS		SEG32		TIMx_IC1	EVENT OUT
PD13	-	-	TIM4_CH2	-	-	-	-	-		SEG33		TIMx_IC2	EVENT OUT
PD14	-	-	TIM4_CH3	-	-	-	-	-		SEG34		TIMx_IC3	EVENT OUT
PD15	-	-	TIM4_CH4	-	-	-	-	-		SEG35		TIMx_IC4	EVENT OUT
PE0	-	-	TIM4_ETR	TIM10_CH1	-	-	-	-		SEG36		TIMx_IC1	EVENT OUT
PE1	-	-	-	TIM11_CH1	-	-	-	-		SEG37		TIMx_IC2	EVENT OUT
PE2	TRACECK	-	TIM3_ETR	-				-		SEG 38		TIMx_IC3	EVENT OUT
PE3	TRACED0	-	TIM3_CH1	-	-	-	-	-		SEG 39		TIMx_IC4	EVENT OUT
PE4	TRACED1	-	TIM3_CH2	-	-	-	-	-		-		TIMx_IC1	EVENT OUT
PE5	TRACED2	-	-	TIM9_CH1	-	-	-	-		-		TIMx_IC2	EVENT OUT
PE6-WKUP3	TRACED3	-	-	TIM9_CH2	-	-	-	-		-		TIMx_IC3	EVENT OUT
PE7	-	-	-	-	-	-	-	-		-		TIMx_IC4	EVENT OUT

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = 3.6 V (for the 1.65 V ≤V_{DD} ≤3.6 V voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 11*.

Figure 10. Pin loading conditions

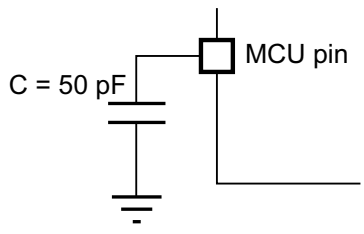
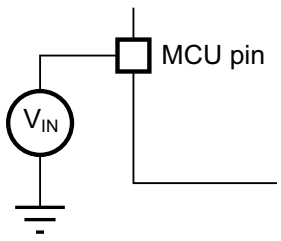


Figure 11. Pin input voltage



4. Positive current injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for maximum allowed input voltage values.
5. A positive injection is induced by $V_{IN} > V_{DD}$ while a negative injection is induced by $V_{IN} < V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11: Voltage characteristics* for the maximum allowed input voltage values.
6. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	150	°C

6.3 Operating conditions

6.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	32	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	32	
f_{PCLK2}	Internal APB2 clock frequency	-	0	32	
V_{DD}	Standard operating voltage	BOR detector disabled	1.65	3.6	V
		BOR detector enabled, at power on	1.8	3.6	
		BOR detector disabled, after power on	1.65	3.6	
V_{DDA}(1)	Analog operating voltage (ADC and DAC not used)	Must be the same voltage as V_{DD}(2)	1.65	3.6	V
	Analog operating voltage (ADC or DAC used)		1.8	3.6	
V_{IN}	I/O input voltage	FT pins; 2.0 V ≤V_{DD}	-0.3	5.5(3)	V
		FT pins; V_{DD} < 2.0 V	-0.3	5.25(3)	
		BOOT0 pin	0	5.5	
		Any other pin	-0.3	V_{DD}+0.3	
P_D	Power dissipation at TA = 85 °C for suffix 6 or TA = 105 °C for suffix 7(4)	LQFP48 package	-	364	mW
		LQFP100 package	-	465	
		LQFP64 package	-	435	
		UFQFPN48 package	-	625	
		UFBGA100	-	339	
		WLCSP63 package	-	408	

Table 15. Embedded reset and power control block characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{BOR3}	Brown-out reset threshold 3	Falling edge	2.45	2.55	2.6	V
		Rising edge	2.54	2.66	2.7	
V_{BOR4}	Brown-out reset threshold 4	Falling edge	2.68	2.8	2.85	
		Rising edge	2.78	2.9	2.95	
V_{PVD0}	Programmable voltage detector threshold 0	Falling edge	1.8	1.85	1.88	
		Rising edge	1.88	1.94	1.99	
V_{PVD1}	PVD threshold 1	Falling edge	1.98	2.04	2.09	
		Rising edge	2.08	2.14	2.18	
V_{PVD2}	PVD threshold 2	Falling edge	2.20	2.24	2.28	
		Rising edge	2.28	2.34	2.38	
V_{PVD3}	PVD threshold 3	Falling edge	2.39	2.44	2.48	
		Rising edge	2.47	2.54	2.58	
V_{PVD4}	PVD threshold 4	Falling edge	2.57	2.64	2.69	
		Rising edge	2.68	2.74	2.79	
V_{PVD5}	PVD threshold 5	Falling edge	2.77	2.83	2.88	
		Rising edge	2.87	2.94	2.99	
V_{PVD6}	PVD threshold 6	Falling edge	2.97	3.05	3.09	
		Rising edge	3.08	3.15	3.20	
V_{hyst}	Hysteresis voltage	BOR0 threshold	-	40	-	mV
		All BOR and PVD thresholds excepting BOR0	-	100	-	

1. Guaranteed by characterization results.
2. Valid for device version without BOR at power up. Please see option “D” in Ordering information scheme for more details.

Table 21. Current consumption in Low-power run mode

Symbol	Parameter	Conditions			Typ	Max(1)	Unit
$I_{DD\ (LP\ Run)}$	Supply current in Low-power run mode	All peripherals OFF, code executed from RAM, Flash switched OFF, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	8.6	12	µA
				T_A = 85 °C	19	25	
				T_A = 105 °C	35	47	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A =-40 °C to 25 °C	14	16	
				T_A = 85 °C	24	29	
				T_A = 105 °C	40	51	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	26	29	
				T_A = 55 °C	28	31	
				T_A = 85 °C	36	42	
				T_A = 105 °C	52	64	
		All peripherals OFF, code executed from Flash, V_{DD} from 1.65 V to 3.6 V	MSI clock, 65 kHz f_{HCLK} = 32 kHz	T_A = -40 °C to 25 °C	20	24	
				T_A = 85 °C	32	37	
				T_A = 105 °C	49	61	
			MSI clock, 65 kHz f_{HCLK} = 65 kHz	T_A = -40 °C to 25 °C	26	30	
				T_A = 85 °C	38	44	
				T_A = 105 °C	55	67	
			MSI clock, 131 kHz f_{HCLK} = 131 kHz	T_A = -40 °C to 25 °C	41	46	
				T_A = 55 °C	44	50	
				T_A = 85 °C	56	87	
				T_A = 105 °C	73	110	
I_{DD} max (LP Run)	Max allowed current in Low-power run mode	V_{DD} from 1.65 V to 3.6 V	-	-	-	200	

1. Guaranteed by characterization results, unless otherwise specified.

Table 23. Typical and maximum current consumptions in Stop mode (continued)

Symbol	Parameter	Conditions		Typ	Max(1)	Unit
I_{DD} (Stop)	Supply current in Stop mode (RTC disabled)	Regulator in LP mode, HSI and HSE OFF, independent watchdog and LSI enabled	T_A = -40°C to 25°C	1.8	2.2	µA
		Regulator in LP mode, LSI, HSI and HSE OFF (no independent watchdog)	T_A = -40°C to 25°C	0.435	1	
			T_A = 55°C	0.99	3	
			T_A= 85°C	2.4	9	
			T_A = 105°C	5.5	22(5)	
I_{DD} (WU from Stop)	Supply current during wakeup from Stop mode	MSI = 4.2 MHz	T_A = -40°C to 25°C	2	-	mA
		MSI = 1.05 MHz		1.45	-	
		MSI = 65 kHz(6)		1.45	-	

1. Guaranteed by characterization results, unless otherwise specified.
2. LCD enabled with external VLCD, static duty, division ratio = 256, all pixels active, no LCD connected.
3. LCD enabled with external VLCD, 1/8 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
4. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.
5. Guaranteed by test in production.
6. When MSI = 64 kHz, the RMS current is measured over the first 15 µs following the wakeup event. For the remaining part of the wakeup period, the current corresponds the Run mode current.

Low-speed external user clock generated from an external source

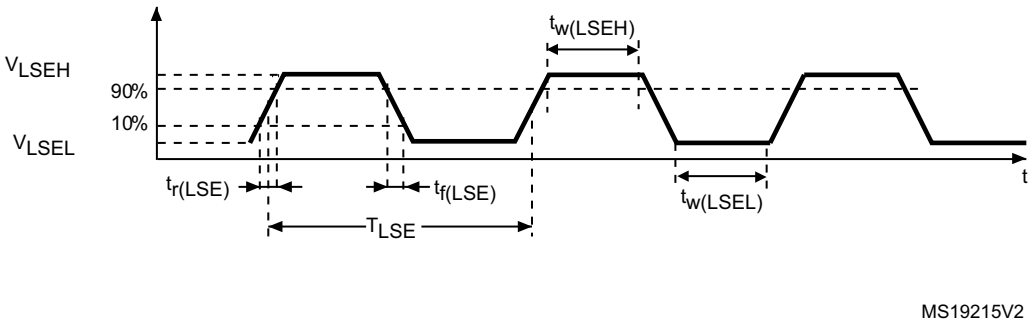
The characteristics given in the following table result from tests performed using a low-speed external clock source, and under the conditions summarized in *Table 14*.

Table 28. Low-speed external user clock characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	1	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage		$0.7V_{DD}$	-	V_{DD}	V
V_{LSEL}	OSC32_IN input pin low level voltage		V_{SS}	-	$0.3V_{DD}$	
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time		465	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time		-	-	10	
$C_{IN(LSE)}$	OSC32_IN input capacitance	-	-	0.6	-	pF

1. Guaranteed by design.

Figure 16. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 1 to 24 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in *Table 29*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 19* and *Table 45*, respectively.

Unless otherwise specified, the parameters given in *Table 45* are derived from tests performed under the conditions summarized in *Table 14*.

Table 45. I/O AC characteristics(1)

OSPEEDRx [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Max(2)	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	400	kHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	400	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	625	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	625	
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	2	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	1	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	125	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	250	
10	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	10	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	2	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 50 pF, V_{DD} = 2.7 V to 3.6 V	-	25	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	125	
11	$F_{max(IO)out}$	Maximum frequency(3)	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	50	MHz
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	8	
	$t_{f(IO)out}$ $t_{r(IO)out}$	Output rise and fall time	C_L = 30 pF, V_{DD} = 2.7 V to 3.6 V	-	5	ns
			C_L = 50 pF, V_{DD} = 1.65 V to 2.7 V	-	30	
-	t_{EXTIpw}	Pulse width of external signals detected by the EXTI controller	-	8	-	

1. The I/O speed is configured using the OSPEEDRx[1:0] bits. Refer to the STM32L151xx, STM32L152xx and STM32L162xx reference manual for a description of GPIO Port configuration register.
2. Guaranteed by design.
3. The maximum frequency is defined in *Figure 19*.

Figure 22. SPI timing diagram - slave mode and CPHA = 0

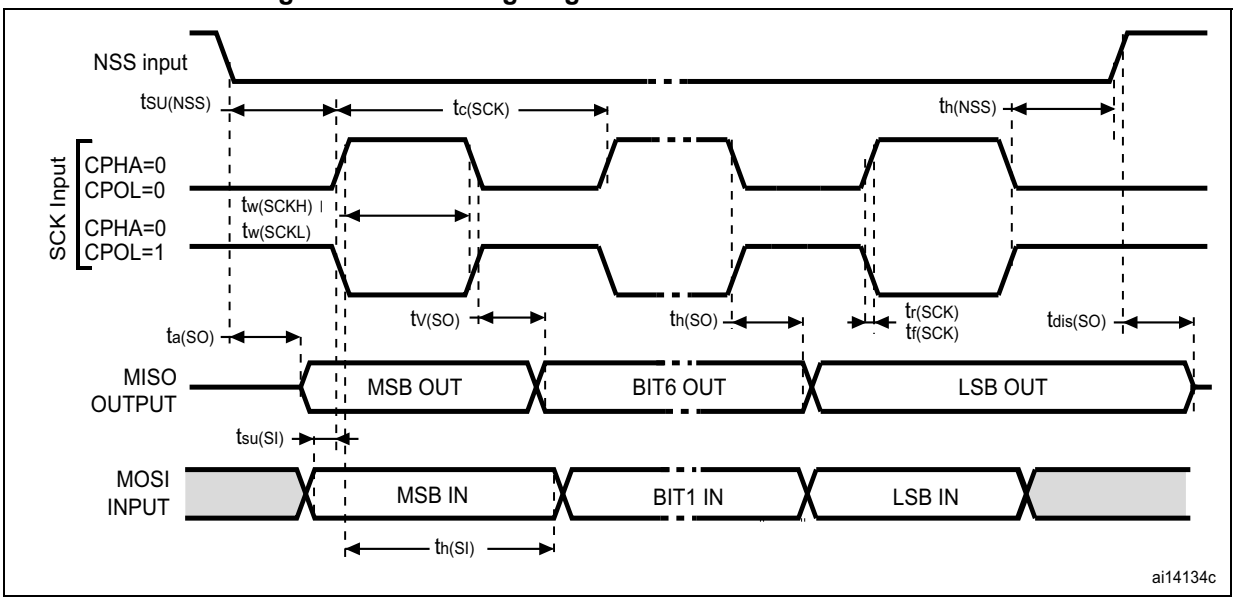
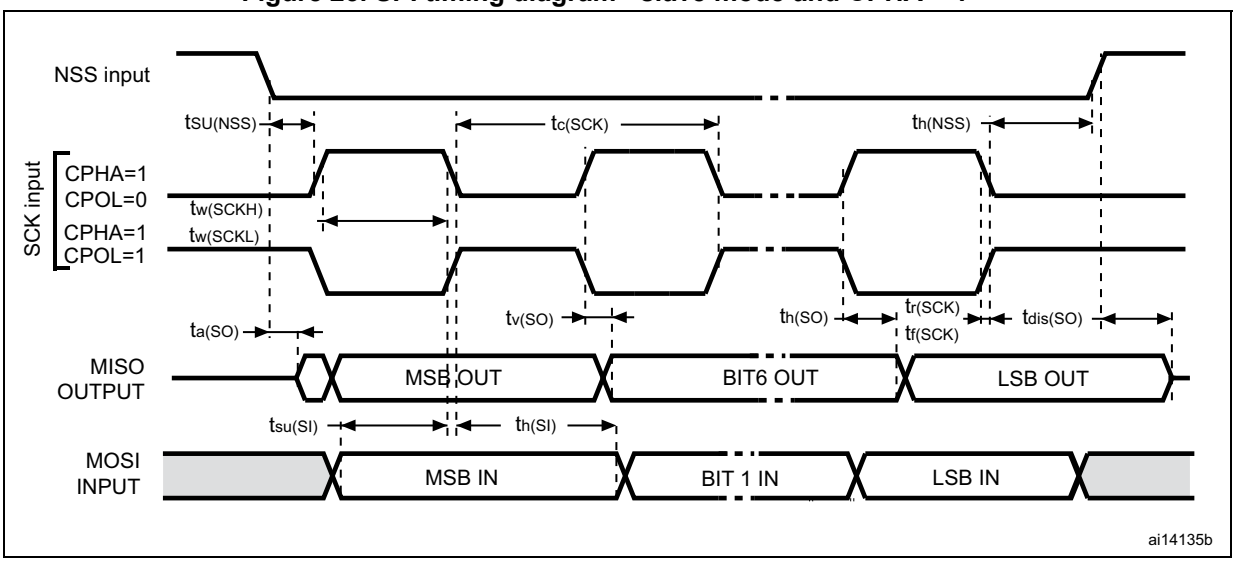


Figure 23. SPI timing diagram - slave mode and CPHA = 1(1)



1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

6.3.20 Temperature sensor characteristics

Table 61. Temperature sensor calibration values

Calibration value name	Description	Memory address
TS_CAL1	TS ADC raw data acquired at temperature of 30 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FA - 0x1FF8 00FB
TS_CAL2	TS ADC raw data acquired at temperature of 110 °C ±5 °C V_{DDA}= 3 V ±10 mV	0x1FF8 00FE - 0x1FF8 00FF

Table 62. Temperature sensor characteristics

Symbol	Parameter	Min	Typ	Max	Unit
T_L(1)	V_{SENSE} linearity with temperature	-	±1	±2	°C
Avg_Slope(1)	Average slope	1.48	1.61	1.75	mV/°C
V_{110}	Voltage at 110°C ±5°C(2)	612	626.8	641.5	mV
$I_{DDA(TEMP)}$(3)	Current consumption	-	3.4	6	µA
t_{START}(3)	Startup time	-	-	10	µs
T_{S_temp}(3)	ADC sampling time when reading the temperature	4	-	-	

1. Guaranteed by characterization results.
2. Measured at V_{DD} = 3 V ±10 mV. V110 ADC conversion result is stored in the TS_CAL2 byte.
3. Guaranteed by design.

6.3.21 Comparator

Table 63. Comparator 1 characteristics

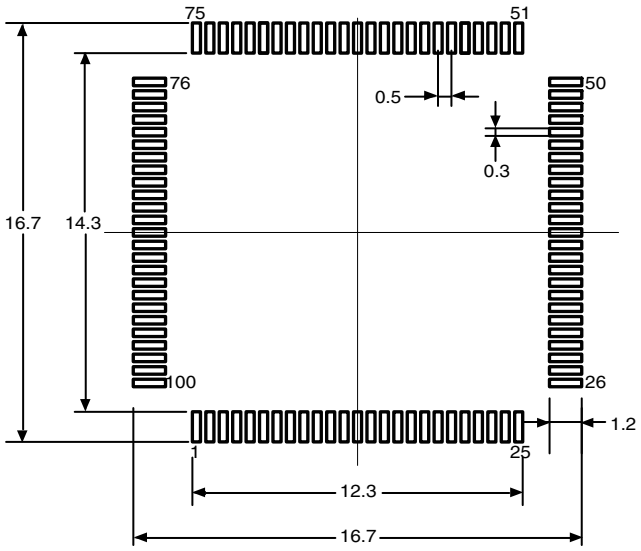
Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
V_{DDA}	Analog supply voltage	-	1.65		3.6	V
R_{400K}	R_{400K} value	-	-	400	-	kΩ
R_{10K}	R_{10K} value	-	-	10	-	
V_{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V
t_{START}	Comparator startup time	-	-	7	10	µs
td	Propagation delay(2)	-	-	3	10	
Voffset	Comparator offset	-	-	±3	±10	mV
$d_{Voffset}$/dt	Comparator offset variation in worst voltage stress conditions	V_{DDA} = 3.6 V V_{IN+} = 0 V V_{IN-} = V_{REFINT} T_A = 25 °C	0	1.5	10	mV/1000 h
I_{COMP1}	Current consumption(3)	-	-	160	260	nA

Table 66. LQPF100, 14 x 14 mm, 100-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	15.800	16.000	16.200	0.6220	0.6299	0.6378
D1	13.800	14.000	14.200	0.5433	0.5512	0.5591
D3	-	12.000	-	-	0.4724	-
E	15.800	16.000	16.200	0.6220	0.6299	0.6378
E1	13.800	14.000	14.200	0.5433	0.5512	0.5591
E3	-	12.000	-	-	0.4724	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 33. LQFP100, 14 x 14 mm, 100-pin low-profile quad flat package recommended footprint



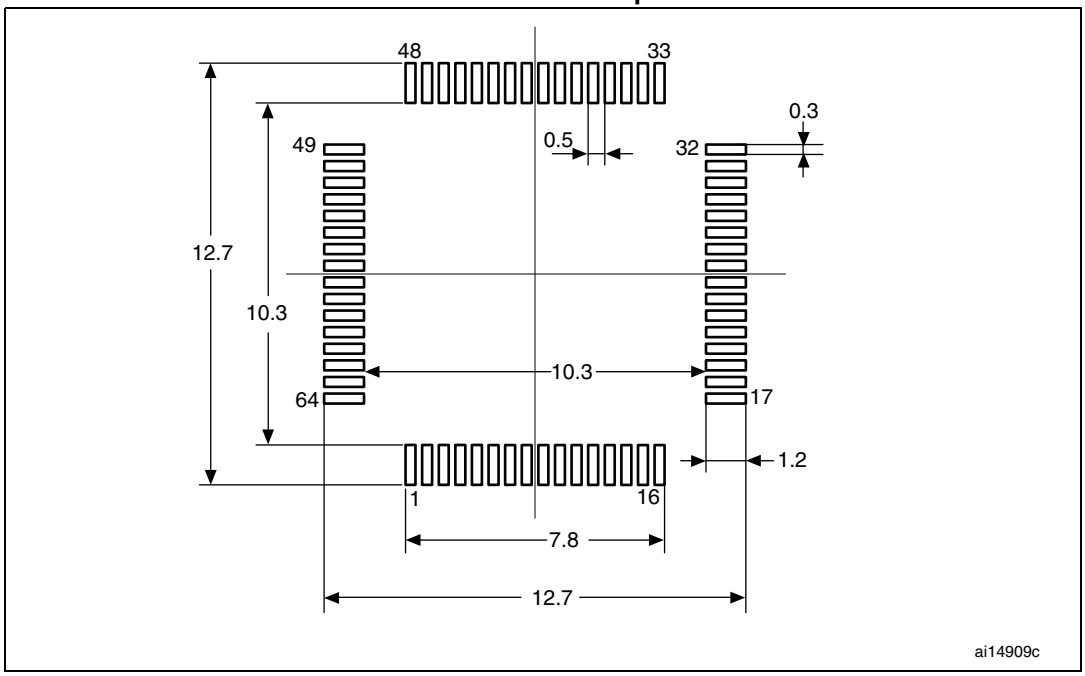
1. Dimensions are in millimeters.

Table 67. LQFP64, 10 x 10 mm 64-pin low-profile quad flat package mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
E3	-	7.500	-	-	0.2953	-
e	-	0.500	-	-	0.0197	-
K	0°	3.5°	7°	0°	3.5°	7°
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 36. LQFP64, 10 x 10 mm, 64-pin low-profile quad flat package recommended footprint



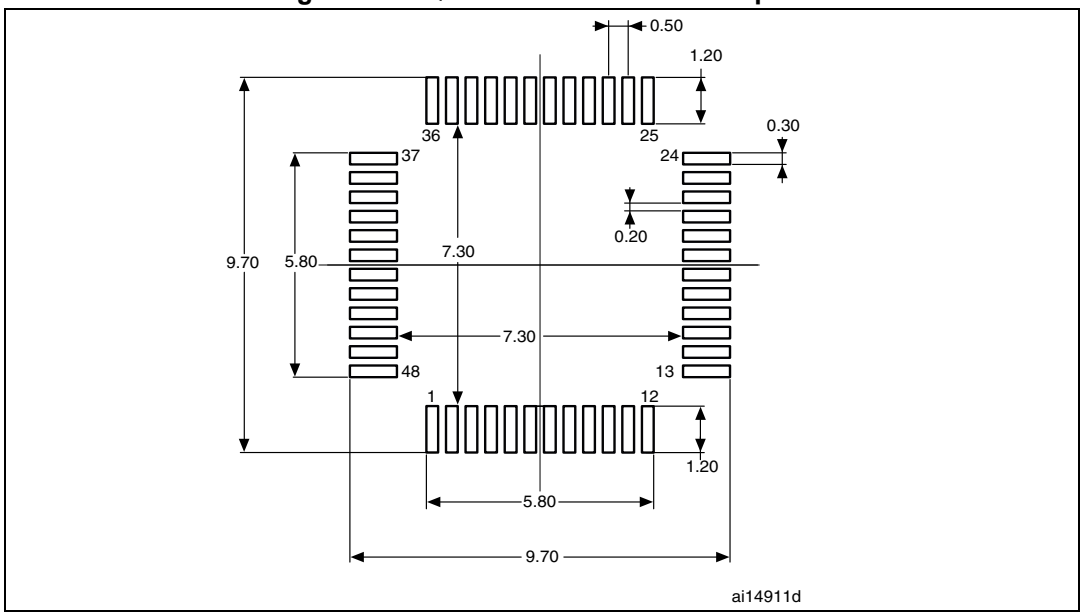
1. Dimensions are in millimeters.

Table 68. LQFP48, 7 x 7 mm, 48-pin low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	8.800	9.000	9.200	0.3465	0.3543	0.3622
D1	6.800	7.000	7.200	0.2677	0.2756	0.2835
D3	-	5.500	-	-	0.2165	-
E	8.800	9.000	9.200	0.3465	0.3543	0.3622
E1	6.800	7.000	7.200	0.2677	0.2756	0.2835
E3	-	5.500	-	-	0.2165	-
e	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0°	3.5°	7°	0°	3.5°	7°
ccc	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 39. LQFP48 recommended footprint



1. Dimensions are in millimeters.

8 Part numbering

Table 74. STM32L151xC and STM32L152xC ordering information scheme

Example: STM32 L 151 R C T 6 D TR

Device family

STM32 = ARM-based 32-bit microcontroller

Product type

L = Low-power

Device subfamily

151: Devices without LCD

152: Devices with LCD

Pin count

C = 48 pins

U = 63 pins

R = 64 pins

V = 100 pins

Flash memory size

C = 256 Kbytes of Flash memory

Package

H = BGA

T = LQFP

Y = WLCSP

U = UFQFPN

Temperature range

6 = Industrial temperature range, –40 to 85 °C

7 = Industrial temperature range, –40 to 105 °C

Options

No character = V_{DD} range: 1.8 to 3.6 V and BOR enabled

D = V_{DD} range: 1.65 to 3.6 V and BOR disabled

Packing

TR = tape and reel

No character = tray or tube

For a list of available options (speed, package, etc.) or for further information on any aspect of this device, please contact the nearest ST sales office.